

JSW



SMC-99-014B

May 11, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Rég. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/823,148 04/13/04
Chrong Jung Lin et al.
A NOVEL MULTI-LEVEL (4STATE/2-BIT)
STACKED GATE FLASH MEMORY CELL
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INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date *Stephen B. Ackerman* 5/17/04

U.S. Patent 5,714,412 to Liang et al., "Multi-Level, Split-Gate, Flash Memory Cell and Method of Manufacture Thereof," discloses a multi-level flash memory cell as applied to a split-gate.

U.S. Patent 5,877,523 to Liang et al., "Mutli-Level Split-Gate Flash Memory Cell," discloses the structure of a multi-level, split-gate flash memory cell.

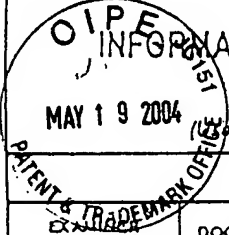
U.S. Patent 5,666,307 to Chang, "PMOS Flash Memory Cell Capable of Multi-Level Threshold Voltage Storage," discloses a PMOS flash memory cell capable of multi-level threshold voltage storage.

U.S. Patent 5,851,881 to Lin et al., "Method of Making MONOS Flash Memory for Multi-Level Logic," discloses a structure and a method of manufacturing split-gate MONOS multi-level logic memory device.

Sincerely,

A handwritten signature in black ink, appearing to read "S.B. Ackerman", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761



INFORMATION DISCLOSURE CITATION IN AN APPLICATION

Docket Number (Optional)

TSMC-99-014B

Application Number

10/823,148

Applicant

Chrong Jung Lin et al.

Filing Date

04/13/04

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5714412	2/3/98	Liang et al.	438	266	12/2/96
	5877523	3/2/99	Liang et al.	257	315	11/20/97
	5666307	9/9/97	Chang	365	185.03	11/14/95
	5851881	12/22/98	Lin et al.	438	261	10/6/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
								YES				NO	

OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.